

EAST Search History (18 pp.)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(US-20040145399-\$).did.	US-PGPUB	OR	OFF	2007/08/18 14:56
L2	1	(US-20040145399-\$).did. and (self-alignment self\$1alignment self\$1align self\$1aligning align\$4 overlap\$4 non\$1overlap\$4)	US-PGPUB	OR	ON	2007/08/18 15:17
L3	8429	("0257213").PN. or ((257/65) or (257/66) or (257/69) or (257/288) or (257/350) or (257/351) or (257/616) or (326/121) or (257/903)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/18 15:18
L4	2	3 and (inverter inverter) and (PFET PMOS PMOSFET PMISFET) and (germanium Ge) and (stack\$3 near10 (transistor MOS MOSFET MIS MISFET TFT CMOS CMOSFET)) and (self-alignment self-align self\$1alignment self\$1align self near1 (align alignment))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/18 15:22
L5	0	(arup near1 bhattacharyya).in. and (inverter inverter) and (PFET PMOS PMOSFET PMISFET) and (germanium Ge) and (stack\$3 near10 (transistor MOS MOSFET MIS MISFET TFT CMOS CMOSFET)) and (self-alignment self-align self\$1alignment self\$1align self near1 (align alignment))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/18 15:23
L6	0	(arup near1 bhattacharyya).in. and (inverter inverter).clm. and (PFET PMOS PMOSFET PMISFET).clm. and (germanium Ge).clm. and (self-alignment self-align self\$1alignment self\$1align alignment aligned align non\$1overlap non\$1overlapping overlap\$4).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/18 15:25
L7	0	((arup near1 bhattacharyya).in. micron.as.) and (inverter inverter).clm. and (PFET PMOS PMOSFET PMISFET).clm. and (germanium Ge).clm. and (self-alignment self-align self\$1alignment self\$1align alignment aligned align non\$1overlap non\$1overlapping overlap\$4).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/18 15:25

EAST Search History

S1	4	"264914".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/20 09:44
S2	6	"760087".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 06:26
S3	3	("6808971").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 06:26
S4	1	"6429085".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:27
S5	1	"5006913".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:42
S6	1	"4768076".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:43
S7	1	"4692994".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:44
S8	8	((("4692994") or ("4768076") or ("5006913") or ("6429085")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 07:44
S9	1	(US-20040145399-\$).did.	US-PGPUB	OR	OFF	2005/09/07 07:45
S10	0	battacharyya.in. and strained and (sige gesi si-ge ge-si silicon adj germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:56
S11	0	battacharyya.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:56
S12	644	bhattacharyya.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:57
S13	73	bhattacharyya.in. and cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:57

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S14	36	bhattacharyya.in. and cmos and (thin adj film TFT) and strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 08:57
S15	36	bhattacharyya.in. and cmos and (thin adj film TFT) and strained and (sige gesi si-ge ge-si silicon adj germanium germanium adj silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 08:58
S16	35	bhattacharyya.in. and cmos and (thin adj film TFT) and strained.clm. and (sige gesi si-ge ge-si silicon adj germanium germanium adj silicon). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:17
S17	11	(inverter invertor).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4"Ge.sub."\$4 "Ge.sub."\$4"Si.sub."\$4 Si-Ge Ge-Si)).ti,ab, clm. and strained.ti,ab,clm. and (monocrystalline single adj crystal). ti,ab,clm. and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:24
S18	11	(inverter invertor CMOS).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge. sub."\$4 "Si.sub."\$4"Ge.sub."\$4 "Ge. sub."\$4"Si.sub."\$4 Si-Ge Ge-Si)).ti, ab,clm. and strained.ti,ab,clm. and (monocrystalline single adj crystal). ti,ab,clm. and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:26
S19	34	(inverter invertor CMOS).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge. sub."\$4 "Si.sub."\$4"Ge.sub."\$4 "Ge. sub."\$4"Si.sub."\$4 Si-Ge Ge-Si)).ti, ab,clm. and strained.ti,ab,clm. and (monocrystalline single adj crystal). ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:26
S20	5	(inverter invertor CMOS).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge. sub."\$4 "Si.sub."\$4"Ge.sub."\$4 "Ge. sub."\$4"Si.sub."\$4 Si-Ge Ge-Si)).ti, ab,clm. and strained.ti,ab,clm. and (monocrystalline single adj crystal). ti,ab,clm. and @ad<"20020311"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 10:33

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S21	2	("5298452").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 10:46
S22	191	speed near4 CMOS near4 (inverter inverter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 10:47
S23	1	improve near4 speed near4 CMOS near4 (inverter inverter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 10:49
S24	44	("higher" improve improvement improvement increase increasing) near4 speed near4 CMOS near4 (inverter inverter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 11:06
S25	49	("higher" improve improvement improvement increase increasing) near4 speed near4 CMOS near4 (inverter inverter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 11:09
S26	14	("higher" improve improvement improvement increase increasing) near4 speed near4 CMOS near4 (inverter inverter) and (single adj crystal monocrystal monocrystalline)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 11:08
S27	23	"6251751"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 13:41
S28	18	S27 and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 13:42
S29	2	("6251751").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 13:42
S30	1	S29 and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 14:19

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S31	2	("20020125471").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 14:22
S32	1	S31 and (polysilicon polycrystalline poly poly-Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 14:22
S33	1	S31 and (polysilicon polycrystalline poly poly-Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:25
S34	28	polycrystalline near4 silicon adj germanium near10 method.clm. and "438"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:26
S35	8	polycrystalline near1 silicon adj germanium near4 method.clm. and "438"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:27
S36	1	polycrystalline near1 silicon adj germanium near4 method.clm. and "438"/\$7.ccls. and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:27
S37	156	silicon adj germanium near4 band adj gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:05
S38	2	silicon adj germanium near4 band adj gap near4 wide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:05
S39	156	silicon adj germanium near4 band adj gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:12
S40	37	relaxed near20 strained.clm. and transistor.ti,ab,clm. and (single adj crystal monocrystalline).clm. and silicon and germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 16:14

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S41	10	relaxed near20 strained.clm. and transistor.ti,ab,clm. and (single adj crystal monocrystalline).clm. and silicon and germanium	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 16:20
S42	4900	((257/76) or (257/213) or (257/288) or (257/347) or (257/350) or (257/351) or (257/616)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/09/07 16:20
S43	139	S42 and relaxed and strained and (Se-Ge Ge-Si (silicon near1 germanium) SiGe "Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4"Ge.sub."\$4 "Ge.sub."\$4"Si.sub."\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:22
S44	16	S42 and relaxed and strained and (Se-Ge Ge-Si (silicon near1 germanium) SiGe "Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4"Ge.sub."\$4 "Ge.sub."\$4"Si.sub."\$4) and (inverter invertor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:22
S45	4	((("6251751") or ("5298452"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 21:18
S46	2	("20020125471").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 22:05
S47	1418	(pfet pmos pmosfet pmisfet) near6 (above below) near6 (nfet nmos nmosfet nmisfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 22:06
S48	1480	(pfet pmos pmosfet pmisfet) near6 (above below) near6 (nfet nmos nmosfet nmisfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:06
S49	363	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:07
S50	44	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) and (silicon si) near3 (ge germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:07

EAST Search History

S51	57	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) and ((silicon si) near3 (ge germanium) sige silicon-germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:08
S52	25	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) and ((silicon si) near3 (ge germanium) sige silicon-germanium)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:09
S53	25	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) and ((silicon si) near3 (ge germanium) sige silicon-germanium) and @ad<"20031004"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:10
S54	5	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) near4 invert?r and ((silicon si) near3 (ge germanium) sige silicon-germanium) and @ad<"20031004"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:12
S55	5	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) near4 invert?r and (((silicon si) near3 (ge germanium)) sige silicon-germanium) and @ad<"20031004"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:19
S56	107	stack\$3 near4 (pfet pmos pmosfet pmisfet) near4 (nfet nmos nmosfet nmisfet) and (inverter invertor)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:43
S57	1	"4692994".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:23
S58	1	"3793721".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:24
S59	1	"4467518".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:24
S60	1	"4489478".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:24
S61	1	"4498226".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:25
S62	1	"4502202".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:26
S63	1	"4555843".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:26

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S64	1	"4603468".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:26
S65	1	"4649627".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:26
S66	179	stack\$3 near4 (pfet pmos pmosfet pmisfet) near4 (nfet nmos nmosfet nmisfet)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:43
S67	1	(US-20040145399-\$).did.	US-PGPUB	OR	OFF	2006/01/29 08:25
S68	0	S67 and composition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 08:25
S69	1	S67 and semiconductor adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 08:25
S70	1	S67 and semiconductor adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 08:43
S71	252	graded near2 contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 08:43
S72	0	graded near2 contact and (stack stacking stacked) near4 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 10:26
S73	0	(grade grading graded) near2 (contact via) and (stack stacking stacked) near4 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 10:26
S74	5	(grade grading graded) near2 (contact via interconnect interconnection interconnexion) and (stack stacking stacked) near4 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 10:26
S75	1	(US-20040145399-\$).did.	US-PGPUB	OR	OFF	2006/01/29 10:51
S76	0	(US-20040145399-\$).did. and (composition composed grade graded grading)	US-PGPUB	OR	ON	2006/01/29 10:52

EAST Search History

S77	1	(US-20040145399-\$.did. and (composition composed grade graded grading doping concentration)	US-PGPUB	OR	ON	2006/01/29 11:31
S78	4	cmos adj inverter near6 computer.ti, ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:32
S79	4	cmos adj inverter near20 computer. ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:32
S80	22	cmos adj inverter.ti,ab,clm. and computer.ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:33
S81	0	cmos adj inverter near10 (logic adj circuit).ti,ab,clm. and computer near10 (logic adj circuit).ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:34
S82	0	cmos adj inverter near20 (logic adj circuit).ti,ab,clm. and computer near20 (logic adj circuit).ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:35
S83	10	cmos adj inverter near3 computer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 11:37
S84	7	cmos adj inverter near6 computer not bhattacharyya.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 11:42
S85	2	("5774008").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 12:10
S86	13	strained near10 relaxed near10 lattice and CMOS near1 invert?r	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 13:27
S87	2	("6251751").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 13:57
S88	6622	((257/76) or (257/213) or (257/288) or (257/347) or (257/350) or (257/351) or (257/616)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 13:57

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S89	2	S88 and (sige silicon adj germanium).ti,ab,clm. and cmos near1 invert?r and (stack stacking stacked) near10 (pfet nfet pmos pmosfet pmisfet nmis nmisfet nmos nmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 13:59
S90	2	S88 and (sige silicon adj germanium).ti,ab,clm. and cmos near1 invert?r and (stack stacking stacked) near10 (pfet nfet pmos pmosfet pmisfet nmis nmisfet nmos nmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 14:00
S91	2	("6882010").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 14:01
S92	2	("6649980").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/12 16:18
S93	5	"454304".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/12 16:24
S94	2	"6888750".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/12 16:25
S95	2	("20030030091").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/12 18:27
S96	38	(single adj crystal monocrystalline) near6 relaxed and tensile near4 strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 18:28
S97	36	(single adj crystal monocrystalline) near3 relaxed and tensile near4 strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 18:28

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S98	3	"6800892".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/01 13:10
S99	6	((("20040179391") or ("20040155317") or ("20040178826")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/01 15:33
S10 0	4	stacked adj (TFT thin adj film adj transistor) and (silicon-germanium sige silicon near1 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 15:38
S10 1	68	(stacking stack stacked) near2 (TFT thin adj film adj transistor) and (silicon-germanium sige silicon near1 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 15:41
S10 2	10	(stacking stack stacked) near2 (TFT thin adj film adj transistor) and (silicon-germanium sige silicon near1 germanium) and relaxed near6 strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 15:42
S10 3	3	(stacking stack stacked) near2 (TFT thin adj film adj transistor) and (silicon-germanium sige silicon near1 germanium) and (CTE thermal adj expansion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 15:46
S10 4	453	(stacking stack stacked) near2 (TFT thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 15:46
S10 5	101	(stacking stack stacked) near2 (TFT thin adj film adj transistor).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 15:50
S10 6	23110861	(stacking stack stacked) near2 (TFT thin adj film adj transistor)".ti,ab, clm.and" @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 15:51
S10 7	53	(stacking stack stacked) near2 (TFT thin adj film adj transistor).ti,ab,clm. and @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 15:54

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S10 8	4	(stacking stack stacked) near2 (TFT thin adj film adj transistor).ti,ab,clm. and @ad<"20021004" and (SiGe si-ge silicon near1 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:14
S11 1	1	"6888750".pn. and control adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/01 19:24
S11 2	1	"6888750".pn. and control adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 19:24
S11 3	1428	strained and relaxed and (silicon adj germanium sige silicon-germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 19:25
S11 4	1085	strained and relaxed and (silicon adj germanium sige silicon-germanium) and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 19:25
S11 5	64	strained and relaxed and (silicon adj germanium sige silicon-germanium) and (tft thin adj film adj transistor) and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 19:26
S11 6	9	strained and relaxed and (silicon adj germanium sige silicon-germanium) and (tft thin adj film adj transistor) and "257"/\$7.ccls. and @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 19:29
S11 7	9	strained and relaxed and (tft thin adj film adj transistor) and "257"/\$7.ccls. and @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 19:30
S11 8	13	strained and relaxed and (tft thin adj film adj transistor) and @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 19:31
S11 9	611	first adj semiconductor adj (film layer) and second adj semiconductor adj (film layer) and (tft thin adj film adj transistor) and @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 19:32

EAST Search History

S12 0	0	underfilm near10 (silicon-germanium sige silicon adj germanium germanium adj silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 09:11
S12 1	2	underfilm and (silicon-germanium sige silicon adj germanium germanium adj silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 09:12
S12 2	0	underfilm and (silicon-germanium sige silicon adj germanium germanium adj silicon) and (tft thin adj film adj transistor "SOI")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:17
S12 3	1585	nickel and (silicon-germanium silicon near1 germanium sige) and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:18
S12 4	541	nickel near10 catalyst and (silicon-germanium silicon near1 germanium sige) and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:18
S12 5	0	nickel near10 catalyst near10 (silicon-germanium silicon near1 germanium sige) and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:18
S12 6	2	nickel near10 catalyst with (silicon-germanium silicon near1 germanium sige) and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:19
S12 7	48	nickel with (silicon-germanium silicon near1 germanium sige) and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 11:25
S12 8	918	cmos adj inverter.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 11:25
S12 9	45	cmos adj inverter.ti. and "257"/\$7. ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 11:25

EAST Search History

S13 0	16	cmos adj inverter.ti. and "327"/\$7. ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 11:26
S13 1	6	cmos adj inverter.ti. and "365"/\$7. ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 11:26
S13 2	44	cmos adj inverter.ti.	USPAT	OR	ON	2006/11/02 11:28
S13 3	7740	((257/65) or (257/66) or (257/69) or (257/213) or (257/288) or (257/350) or (257/351) or (257/616) or (326/121)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 11:29
S13 4	3	S133 and (silicon-germanium silicon near1 germanium sige) and (invert?r near1 CMOS) and (composition compositional compositionally) and stack\$3 near1 (transistor tft mosfet mos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 11:33
S13 5	58	bhattacharyya.in. and tft and germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 11:38
S13 6	0	(bhattacharyya.in. micron.as.) and (composition compositional\$2).clm. and (germanium near1 silicon silicon-germanium sige).clm. and invert?1r.clm. and first near3 (layer film).clm. and second near3 (layer film).clm. and nfet.clm. and pfet. clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 11:42
S13 7	0	(bhattacharyya.in. micron.as.) and (composition compositional\$2).clm. and (germanium near1 silicon silicon-germanium sige).clm. and invert?1r.clm. and first near3 (layer film).clm. and second near3 (layer film).clm. and (tft nfet).clm. and (tft pfet).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 11:43

EAST Search History

S13 8	0	(bhattacharyya.in. micron.as.) and (composition compositional\$2).clm. and (germanium near1 silicon silicon-germanium sige).clm. and invert?1r.clm. and first near3 (layer film).clm. and second near3 (layer film).clm. and (tft thin adj film adj transistor nfet).clm. and (tft thin adj film adj transistor pfet).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 11:43
S13 9	0	(bhattacharyya.in. micron.as.) and (composition compositional\$2).clm. and (germanium near1 silicon silicon-germanium sige).clm. and invert?1r.clm. and first near3 (layer film).clm. and second near3 (layer film).clm. and (tft thin adj film adj transistor nfet pfet).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 11:48
S14 0	40	((("4333808") or ("4488262") or ("4648179") or ("4870470") or ("4776922") or ("5811870") or ("5874778") or ("6344373") or ("7012297") or ("6700771") or ("6933572") or ("6743681") or ("6784480") or ("7132348") or ("6943065") or ("6828632") or ("6903001") or ("6917078") or ("6903969") or ("7042027") or ("6759712") or ("6873015") or ("6998683") or ("6882010") or ("6768156") or ("6800892") or ("6812504") or ("7042052") or ("6713810") or ("7026690") or ("6998667") or ("6845034") or ("6900667") or ("6888200") or ("6908798") or ("6873018") or ("6955960") or ("6982457") or ("7130216") or ("7019378") or ("6950340"))).PN.	USPAT; JPO	OR	OFF	2006/11/02 12:20
S14 1	0	("20030030091").PN.	USPAT; JPO	OR	OFF	2006/11/02 15:19
S14 2	1	("20030030091").PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/11/02 12:20
S14 3	0	("20030030091").PN.	USPAT; JPO	OR	OFF	2006/11/02 15:19
S14 4	2	("6888750").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 12:51

EAST Search History

S14 5	0	("tftnear4flash").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 12:51
S14 6	37	tft near4 flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 13:14
S14 7	2	("6882010").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 13:14
S14 8	8022	((257/65) or (257/66) or (257/69) or (257/213) or (257/288) or (257/350) or (257/351) or (257/616) or (326/121)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 13:23
S14 9	23	S148 and invert?r and drain and (field adj effect adj transistor FET PFET NFET NMOSFET PMOSFET NMISFET PMISFET NMOS PMOS) and relaxed and strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 13:37
S15 0	11	((bhattacharyya near3 arup).in. micron.as.) and invert?r.clm. and drain.clm. and (field adj effect adj transistor FET PFET NFET NMOSFET PMOSFET NMISFET PMISFET NMOS PMOS).clm. and relaxed and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 13:27
S15 1	5	((bhattacharyya near3 arup).in. micron.as.) and invert?r.clm. and drain.clm. and (field adj effect adj transistor FET PFET NFET NMOSFET PMOSFET NMISFET PMISFET NMOS PMOS).clm. and signal.clm. and relaxed and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 13:35
S15 2	5	((bhattacharyya near3 arup).in. micron.as.) and invert?r.clm. and drain.clm. and (field adj effect adj transistor FET PFET NFET NMOSFET PMOSFET NMISFET PMISFET NMOS PMOS).clm. and signal.clm. and insulat\$3.clm. and relaxed and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 13:37

EAST Search History

S15 3	5	((bhattacharyya near3 arup).in. micron.as.) and invert?r.clm. and drain.clm. and (field adj effect adj transistor FET PFET NFET NMOSFET PMOSFET NMISFET PMISFET NMOS PMOS).clm. and signal.clm. and insulat\$3.clm. and relaxed and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/17 13:37
S15 4	23	S148 and invert?r and drain and (field adj effect adj transistor FET PFET NFET NMOSFET PMOSFET NMISFET PMISFET NMOS PMOS) and relaxed and strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/17 13:37
S15 5	17073	nand adj gate near6 invert?r	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/16 14:26
S15 6	12968	nand adj gate near3 invert?r	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/16 14:26
S15 7	1879	nand adj gate near3 invert?r.ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/16 14:26
S15 8	540	nand adj gate near1 invert?r.ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/16 14:26
S15 9	94	nand adj gate near1 invert?r.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/16 14:27
S16 0	3604	nand adj gate.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/16 14:33
S16 1	2	("6888750").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/16 14:33

EAST Search History

S16 2	2	("6888750").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/18 15:12
S16 3	0	("inverternear4(flashadjmemoryadja rray)").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/18 15:12
S16 4	1	flash adj memory adj array near6 inverter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/18 15:16
S16 5	1110	eeeprom near4 cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/18 15:24
S16 6	47	eeeprom near4 cmos and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/18 15:24
S16 7	4	((("6888750") or ("6759677"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/18 08:27
S16 8	2	("6882010").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/18 08:27
S16 9	1	(US-20040145399-\$).did.	US-PGPUB	OR	OFF	2007/08/18 11:39
S17 0	0	(US-20040145399-\$).did. and (overlap overlapping non-overlap non-overlapping)	US-PGPUB	OR	OFF	2007/08/18 11:40
S17 1	1	(US-20040145399-\$).did. and (overlap overlapping non-overlap non-overlapping)	US-PGPUB	OR	ON	2007/08/18 11:40
S17 2	1	(US-20040145399-\$).did. and (overlap overlapping non-overlap non-overlapping island)	US-PGPUB	OR	ON	2007/08/18 11:41